



Diode Module

Features

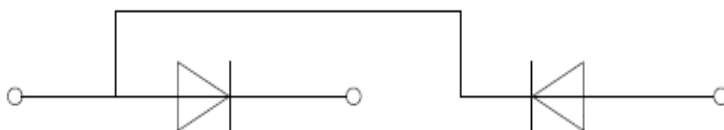
- A package of series of two diodes
- With high thermal conductivity DBC as the Insulation
- Welding by vacuum welding technology, which provide high reliability

Product Summary

Parameter	Value	Unit
V_{RRM}	1600	V
$I_{F(AV)}(@ T_C = 100^\circ\text{C})$	300	A
$I_{FSM}(@ t_p = 10\text{ms})$	11000	A
$V_F(\text{Max})$	1.60	V

Applications

- AC converter
- Inverter
- DC motor



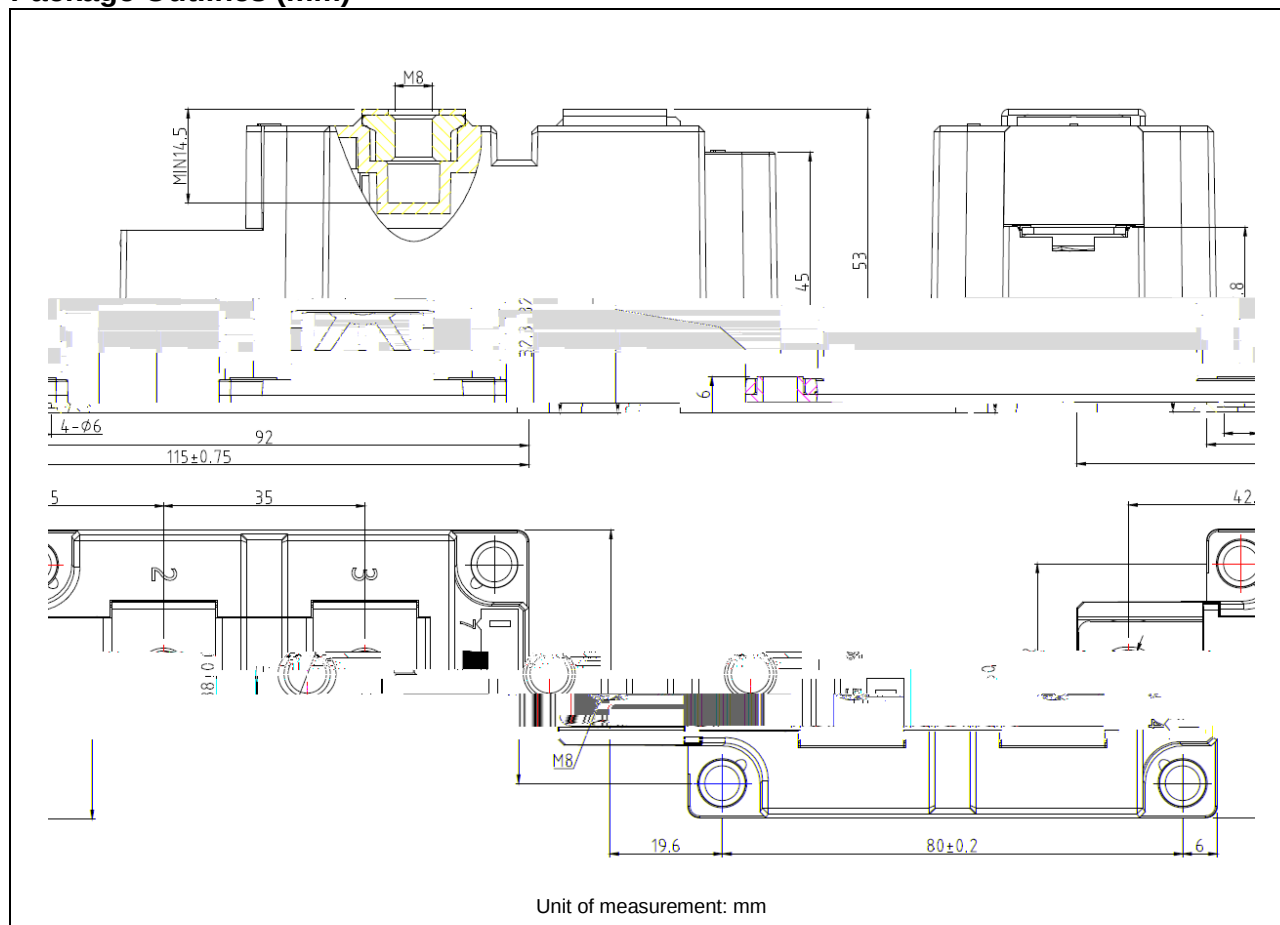
Absolute Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Conditions	Symbol	Values	Unit
Repetitive peak reverse voltage	$T_{vj} = 25^\circ\text{C}$	V_{RRM}	1600	V
Non-repetitive peak reverse voltage	$T_{vj} = 25^\circ\text{C}$	V_{RSM}	1700	V
Average forward current	$T_C = 100^\circ\text{C}$	$I_{F(AV)}$	300	A
Forward surge current	1/2 cycle, Sine wave, 50Hz $T_{vj} = 25$	I_{FSM}	11000	A
I^2t value for fusing		I^2t	605000	A^2s
RMS isolation voltage	A.C 50Hz(1s/1min)	V_{ISO}	3600/3000	V
Junction temperature range		T_J	-40 ~ +150	
Storage temperature range		T_{stg}	-40 ~ +125	

**Electrical Characteristics** (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Conditions	Symbol	Values			Unit
			Min.	Typ.	Max.	
Peak forward voltage	$I_F=900\text{A}$, $t_P=380\mu\text{s}$	V_F			1.60	V
Reverse leakage current	$V_R = V_{RRM}$, $T_{vj} = 25$	I_{RRM}			100	μA
	$V_R = V_{RRM}$, $T_{vj} = 150$				90	mA
Threshold voltage	$T_{vj} = 150$, for power loss calculation only	V_{TO}			0.8	V
Dynamic resistance		r_T			0.75	$\text{m}\Omega$

Thermal Characteristics (@ $T_C = 1-1083\text{ }0\text{ Te}3.24(\text{os})8.3\text{ (s)}-4.7\text{ ()}13.3\text{ }7\text{u. (T)}Tj\text{ }922604\text{ }18\text{MCIC}<</e$

Package Outlines (mm)




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